

EN: This Datasheet is presented by the manufacturer.

Please visit our website for pricing and availability at www.hestore.hu.

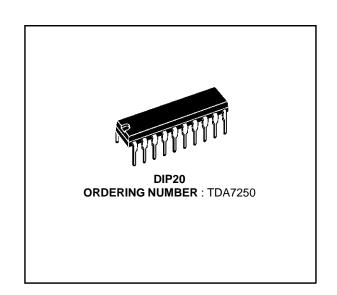


60 W HI-FI DUAL AUDIO DRIVER

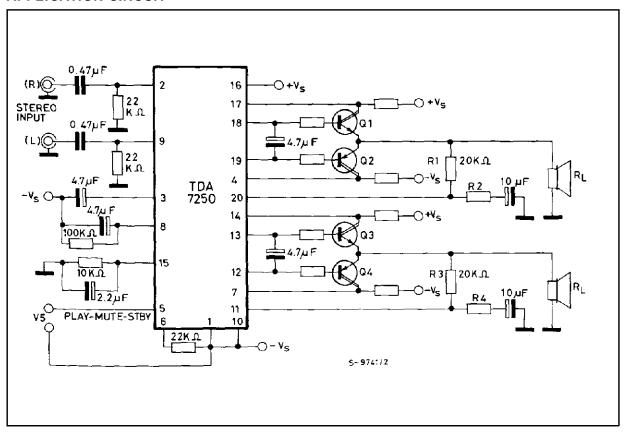
- WIDE SUPPLY VOLTAGE RANGE: 20 TO 90 V (± 10 to ± 45 V)
- VERY LOW DISTORTION
- AUTOMATIC QUIESCENT CURRENT CONTROL FOR THE POWER TRANSISTORS WITHOUT TEMPERATURE SENSE ELEMENTS
- OVERLOAD CURRENT PROTECTION FOR THE POWER TRANSISTORS
- MUTE/STAND-BY FUNCTIONS
- LOW POWER CONSUMPTION
- \blacksquare OUTPUT POWER 60 W/8 Ω AND 100 W/4 Ω

DESCRIPTION

The TDA7250 stereo audio driver is designed to drive two pair of complementary output transistor in the Hi-Fi power amplifiers.

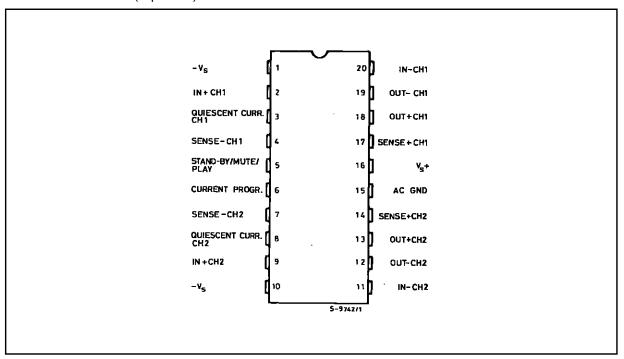


APPLICATION CIRCUIT



March 1995 1/11

PIN CONNECTION (top view)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vs	Supply Voltage	100	V
P _{tot}	Power Dissipation at T _{amb} = 60 °C	1.4	W
T _j , T _{stg}	Storage and Junction Temperature	- 40 to + 150	°C

THERMAL DATA

Symbol	ol Parameter		Value	Unit
R _{th j-amb}	Thermal Resistance Junction-ambient	Max.	65	°C/W

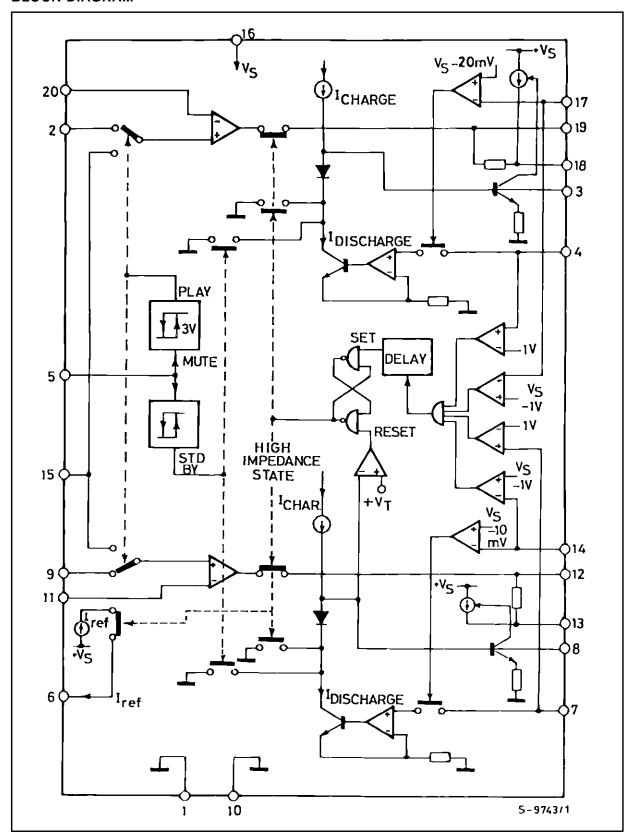


PIN FUNCTIONS

N°	Name	Function			
1	V _S – POWER SUPPLY	Negative Supply Voltage.			
2	NON-INV. INP. CH. 1	Channel 1 Input Signal.			
3	QUIESC. CURRENT CONTR. CAP. CH1	This capacitor works as an integrator, to control the quiescent current to output devices in no-signal conditions on channel 1.			
4	SENSE (-) CH. 1	Negative voltage sense input for overload protection and for automatic quiescent current control.			
5	ST. BY / MUTE / PLAY	Three-functions Terminal. For $V_{\text{IN}} = 1$ to 3 V, the device is in MUTE and only quiescent current flows in the power stages ; - for $V_{\text{IN}} < 1$ V, the device is in STAND-BY mode and no quiescent current is present in the power stages ; - for $V_{\text{IN}} > 3$ V, the devic			
6	CURRENT PROGRAM	High Impedance Power-stages Monitor.			
7	SENSE (-) CH. 2	Negative Voltage Sense Input for Overload Protection and for Automatic Quiescent Current Control.			
8	QUIESC. CURRENT CONTR. CAP. CH. 2	This capacitor works as an integrator, to control the quiescent current to output devices in no-signal conditions on channel 2. If the voltage at its terminals drops under 250 mV, it also resets the device from high-impedance state of output stages.			
9	NON-INV. INP. CH. 2	Channel 2 Input Signals.			
10	V _s – POWER SUPPLY	Negative Supply Voltage.			
11	INVERT. INP. CH. 2	Feedback from Output (channel 2).			
12	OUT (-) CH. 2	Out Signal to Lower Driver Transistor of Channel 2.			
13	OUT (+) CH. 2	Out Signal to Higher Driver Transistor of Channel 2.			
14	SENSE (+) CH. 2	Positive Voltage Sense Input for Overload Protection and for Automatic Quiescent Current Control.			
15	COMMON AC GROUND	AC Input Ground in MUTE Condition.			
16	V _S + POWER SUPPLY	Positive Supply Voltage.			
17	SENSE (+) CH. 1	Positive Voltage Sense Input for Overload Protection and for Automatic Quiescent Current Control.			
18	OUT (+) CH. 1	Out Signal to High Driver Transistor of Channel 1.			
19	OUT (-) CH. 1	Out Signal to Low Driver Transistor of Channel 1.			
20	INVERT. INP. CH. 1	Feedback from Output (channel 1).			



BLOCK DIAGRAM



ELECTRICAL CHARACTERISTICS (T_{amb} = 25 $^{\circ}C$, V_{s} = \pm 35 V, play mode, unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Vs	Supply Voltage		± 10		± 45	V
l _d	Quiescent Drain Current	Stand-by Mode		8		mA
		Play Mode		10	14	
I _b	Input Bias Current			0.2	1	μΑ
Vos	Input Offset Voltage			1	± 10	mV
los	Input Offset Current			100	200	nA
G√	Open Loop Voltage Gain	f = 100 Hz		90		dB
		f = 10 kHz		60		
e _N	Input Noise Voltage	$R_G = 600 \Omega$ B = 20 Hz to 20 kHz		3		μV
SR	Slew Rate			10		V/μs
d	Total Harmonic Distortion	$G_v = 26 \text{ dB}, P_o = 40 \text{ W}$ f = 1 kHz f = 20 kHz		0.004 0.03		% %
V_{opp}	Output Voltage Swing			60		V_{pp}
Po	Output Power (*)	$V_{S} = \pm 35 \text{ V}, R_{L} = 8 \Omega$ $V_{S} = \pm 30 \text{ V}, R_{L} = 8 \Omega$ $V_{S} = \pm 35 \text{ V}, R_{L} = 4 \Omega$		60 40 100		W W W
Ιο	Output Current			± 5		mA
SVR	Supply Voltage Rejection	f = 100 Hz		75		dB
Cs	Channel Separation	f = 1 kHz		75		dB

MUTE / STANDBY/ PLAY FUNCTIONS

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
li	Input Current (pin 5)			0.1		μΑ
V _{th}	Comparator Standby / Mute Threshold (**)		1.0	1.25	1.5	V
Н	Hysteresis Standby / Mute			200		mV
V _{th}	Comparator Mute / Play Threshold (**)		2.4	3.0	3.6	V
Н	Hysteresis Mute / Play			300		mV
	Mute Attenuation	f = 1 kHz		60		dB
Vi	Input Voltage Max. (pin 5)		12 (**)			V

CURRENT SURVEY CIRCUITRY

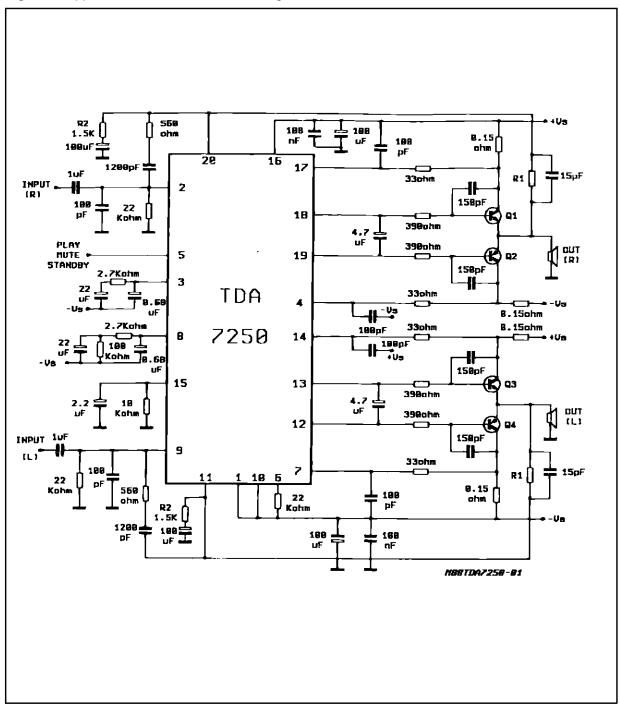
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
	Comparator Reference	to + V _S	0.8	1	1.4	V
		to - V _S	0.8	1	1.4	V
t _d	Delay Time		10			μs

QUIESCENT CURRENT CONTROL

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
	Capacitor Current	Charge	30	60		μΑ
		Discharge	250	500		μΑ
	Comparator Reference	to + V _S	10	20	25	mV
		to - Vs		10		mV



Figure 1: Application Circuit with Power Darlingtons.



Note: Q1/Q2 = Q3/Q4 = TIP 142/TIP147

 $\mathsf{GV} = 1 + \mathsf{R1/R2}$

Figure 2: Output Power vs. Supply Voltage.

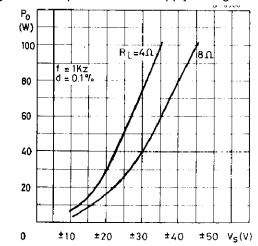


Figure 4: Channel Separation.

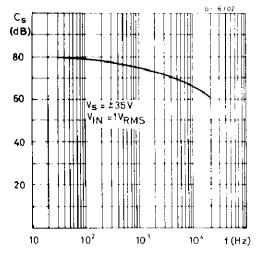


Figure 6: Quiescent Current vs. Supply Voltage.

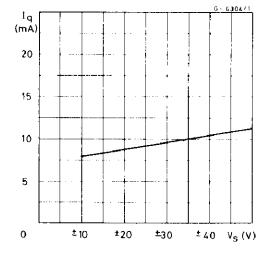


Figure 3: Distortion vs.Output Power (*).

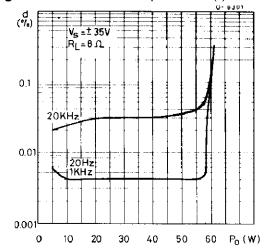


Figure 5 : Supply Voltage Rejection vs. Frequency.

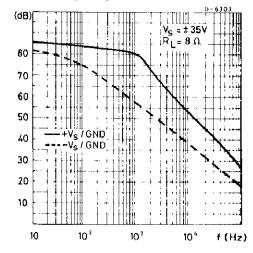


Figure 7: Quiescent Current vs. Tamb.

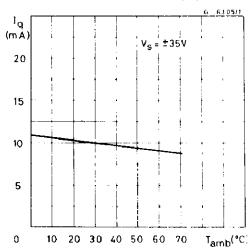


Figure 8 : Total Dissipated Power vs. Output Power (*).

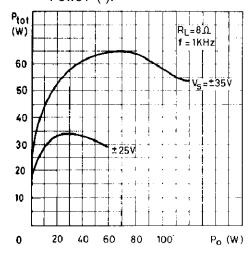
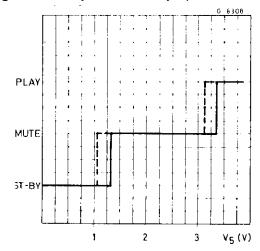
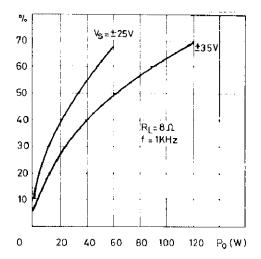


Figure 10: Play-mute Standby Operation.



(*) Complete circuit

Figure 9: Efficiency vs. Output Power (*).



568 oha R2 188 UF 100 1.5K B.15 nF 100pF 188uF 330hm 20 16 17 150pf | 180 R1 INPUT, (C) BD 2 100 22 18 **(6)** 01 Kohm 398ohm PLAY 390ohm I CHI MUTE 4 5 13 STANDBY **(**C) 80 2.7Kphm 3 150pF | 100 TDA 0.68 4 8.15chm 33ohm 7250 2.7Kohm 33ohm 8.15phm 199pF 14 199pF 100 🚣 158pF 0188 BD 912 15 13 Q1 3980hm DUT 390ohm (L) 12 92 INPUT 10F 158pF | 198 9 (L) 7 15pF 330hm R1 0.15 568 22 Kohm 189 ohm μF 1.5K 1288 108 106 υF M88TDA7258-82

Figure 11: Application Circuit Using Power Transistors.

Figure 12: Suggested Transistor Types for Various Loads and Powers.

 $R_L = 8 \Omega$

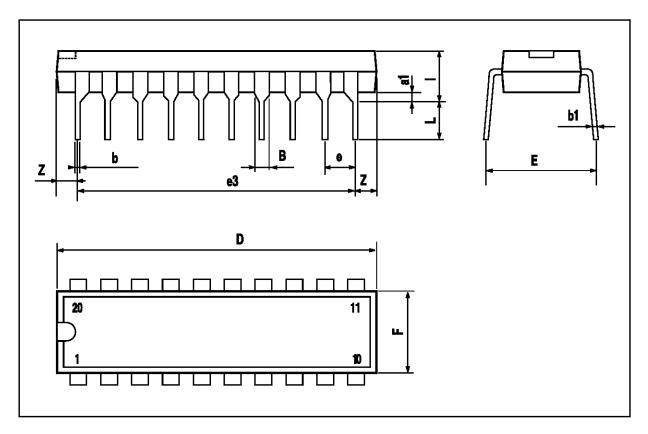
15W	+30W	+50W	+70W
BDX	BDX	BDW	TIP
53/54A	53/54B	93/94B	142/147

_				
	30W	+50W	+90W	+130W
Γ	BDW	BDW	BDV	MJ
ı	93/94A	93/94B	64/65B	11013/11014

 $T_L=4\;\Omega$

DIP20 PACKAGE MECHANICAL DATA

DIM.		mm			inch	
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
В	0.85		1.40	0.033		0.055
b		0.50			0.020	
b1	0.38		0.50	0.015		0.020
D			24.80			0.976
E		8.80			0.346	
е		2.54			0.100	
e3		22.86			0.900	
F			7.10			0.280
I			5.10			0.201
L		3.30			0.130	
Z			1.27			0.050



Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectronics.

© 1995 SGS-THOMSON Microelectronics - All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES

Australia - Brazil - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands - Singapore-Spain - Sweden - Switzerland - Taiwan - Thaliand - United Kingdom - U.S.A.

